

# Irina Bineva

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6961323/publications.pdf>

Version: 2024-02-01

50  
papers

531  
citations

933447

10  
h-index

677142

22  
g-index

50  
all docs

50  
docs citations

50  
times ranked

620  
citing authors

#	ARTICLE	IF	CITATIONS
1	Influence of fast neutron irradiation on the phase composition and optical properties of homogeneous SiO <sub>x</sub> and composite Si-SiO <sub>x</sub> thin films. Journal of Materials Science, 2021, 56, 3197-3209.	3.7	2
2	Modification of surface morphology and lattice order in nanocrystalline ZnO thin films prepared by spin-coating sol-gel method. Journal of Sol-Gel Science and Technology, 2021, 100, 55-67.	2.4	5
3	In-depth evolution of tellurium films deposited by Frequency Assisted Thermal Evaporation in Vacuum (FATEV). Journal of Physics: Conference Series, 2019, 1186, 012026.	0.4	1
4	Ellipsometric study of thin carbon films deposited by pulsed laser deposition. , 2019, , .		0
5	As-doped SnO <sub>2</sub> thin films for use as large area position sensitive photodetector. Thin Solid Films, 2018, 653, 19-23.	1.8	10
6	Surface modification and chemical sensitivity of sol gel deposited nanocrystalline ZnO films. Materials Chemistry and Physics, 2018, 209, 165-171.	4.0	18
7	Optical and electrical properties of TiO <sub>2</sub> /Pt/TiO <sub>2</sub> nanolaminate structures. Journal of Physics: Conference Series, 2018, 992, 012033.	0.4	2
8	Structural and morphological characterization of ternary nanocrystalline Cu-In-S thin films prepared by laser ablation. Journal of Physics: Conference Series, 2017, 794, 012019.	0.4	0
9	As <sub>2</sub> Se <sub>3</sub> thin films deposited by frequency assisted thermal evaporation - morphology and structure. Journal of Physics: Conference Series, 2017, 794, 012015.	0.4	2
10	Sonochemically assisted colloidal route to CdSe quantum dot assemblies: an alternative way to further fine-tune the size-dependent properties. Journal of Materials Science: Materials in Electronics, 2016, 27, 10600-10615.	2.2	2
11	Influence of the thickness on the morphology and sensing ability of thermally-deposited tellurium films. Journal of Physics: Conference Series, 2016, 700, 012037.	0.4	0
12	Photoluminescence from 20 MeV electron beam irradiated homogeneous SiO <sub>x</sub> and composite Si-SiO <sub>x</sub> films. Journal of Physics: Conference Series, 2016, 764, 012018.	0.4	0
13	Crymatics of selenium and tellurium films deposited in vacuum on vibrating substrates. Surface and Coatings Technology, 2016, 307, 542-546.	4.8	6
14	Raman Study of Compositional Variations in Zn <sub>x</sub> Cd <sub>1-x</sub> Se Films Prepared by Thermal Vacuum Evaporation. Journal of Nanoscience and Nanotechnology, 2016, 16, 8513-8518.	0.9	0
15	High energy electron-beam irradiation effects in Si-SiO <sub>x</sub> structures. Journal of Physics: Conference Series, 2016, 682, 012012.	0.4	7
16	Long term ageing changes in structure and morphology of nanocrystalline Zn <sub>x</sub> Cd <sub>1-x</sub> Se thin films. , 2015, , .		0
17	Application of Metal-Oxide-Semiconductor structures containing silicon nanocrystals in radiation dosimetry. Open Physics, 2015, 13, .	1.7	8
18	Charge carrier transport through 3D assemblies of zincblende CdSe and ZnSe quantum dots in weak size-quantization regime. Journal of Materials Science: Materials in Electronics, 2015, 26, 4944-4955.	2.2	4

#	ARTICLE	IF	CITATIONS
19	Structural, compositional and electrical characterization of Si-rich SiO <sub>x</sub> layers suitable for application in light sensors. <i>Materials Science in Semiconductor Processing</i> , 2015, 37, 229-234.	4.0	7
20	UV Dosimeters Based on Metal-Oxide-Semiconductor Structures Containing Si Nanocrystals. <i>Sensor Letters</i> , 2015, 13, 561-564.	0.4	2
21	Resistive characteristics of LSMO/LCMO bi-layers and temperature switching effect of magnetoresistance. <i>Modern Physics Letters B</i> , 2014, 28, 1450096.	1.9	1
22	Deposition and characterization of thin HTS and magnetic perovskite films. <i>Journal of Physics: Conference Series</i> , 2014, 514, 012041.	0.4	3
23	Effect of the composition and annealing on the electron transport in Zn <sub>x</sub> Cd <sub>1-x</sub> Se nanocrystalline films. <i>Journal of Alloys and Compounds</i> , 2014, 586, 650-655.	5.5	4
24	Region of glass formation and main physicochemical properties of glasses from the As <sub>2</sub> Se <sub>3</sub> -Ag <sub>4</sub> SSe-PbTe system. <i>Journal of Alloys and Compounds</i> , 2013, 573, 32-36.	5.5	2
25	Sonochemically Synthesized 3D Assemblies of Close-Packed In <sub>2</sub> S <sub>3</sub> Quantum Dots: Structure, Size Dependent Optical and Electrical Properties. <i>Journal of Physical Chemistry C</i> , 2013, 117, 7303-7314.	3.1	20
26	Effects of the preparation conditions and furnace annealing on the structure and morphology of Zn <sub>0.8</sub> Cd <sub>0.2</sub> Se thin films. , 2013, , .		0
27	Annealing induced changes in ternary nanostructured Zn <sub>x</sub> Cd <sub>1-x</sub> Se thin films: structure and morphology. <i>Journal of Physics: Conference Series</i> , 2012, 398, 012015.	0.4	4
28	Smectic C liquid crystal growth through surface orientation by Zn <sub>x</sub> Cd <sub>1-x</sub> Se thin films. <i>Journal of Physics: Conference Series</i> , 2012, 398, 012036.	0.4	1
29	Al doped ZnO thin films " microstructure, physical and sensor properties. <i>Journal of Physics: Conference Series</i> , 2012, 398, 012019.	0.4	1
30	Temperature Dependence of the Photoluminescence from Ensembles of Amorphous Silicon Nanoparticles with Various Average Sizes. <i>Journal of Nanoscience and Nanotechnology</i> , 2011, 11, 959-965.	0.9	2
31	Electrical characterization of MOS structures with self-organized three-layer gate dielectric containing Si nanocrystals. <i>Journal of Physics: Conference Series</i> , 2010, 253, 012034.	0.4	0
32	Microstructural characterization of thin SiO <sub>x</sub> films obtained by physical vapor deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010, 174, 132-136.	3.5	21
33	Formation of Si Nanocrystals in Thin SiO <sub>2</sub> Films for Memory Device Applications. <i>Materials Science Forum</i> , 2010, 644, 101-104.	0.3	7
34	SPM electrical characterization of Ti/Al Based ohmic contacts for sub-micron devices. , 2010, , .		0
35	Temperature Dependence of the Band-Gap Energy and Sub-Band-Gap Absorption Tails in Strongly Quantized ZnSe Nanocrystals Deposited as Thin Films. <i>Journal of Physical Chemistry C</i> , 2010, 114, 15280-15291.	3.1	58
36	Composition and structure of Zn <sub>x</sub> Cd <sub>1-x</sub> Se single layers prepared by thermal evaporation of ZnSe and CdSe. <i>Journal of Physics: Conference Series</i> , 2010, 253, 012035.	0.4	11

#	ARTICLE	IF	CITATIONS
37	Characterization of ZnSe Nanolayers by Spectroscopic Ellipsometry. Acta Physica Polonica A, 2009, 116, 708-711.	0.5	5
38	Raman Scattering from ZnSe Nanolayers. Acta Physica Polonica A, 2009, 116, 75-77.	0.5	39
39	ZnO Thin Films for Cantilever Coatings: Structural and Mechanical Properties, Observations of Photoplastic Effect. Sensor Letters, 2008, 6, 558-563.	0.4	2
40	Memory effect in MIS structures with amorphous silicon nanoparticles embedded in ultra thin matrix. Journal of Physics and Chemistry of Solids, 2007, 68, 725-728.	4.0	20
41	Dependence of photoluminescence from a-Si nanoparticles on the annealing time and exciting wavelength. Journal of Luminescence, 2007, 126, 7-13.	3.1	2
42	Room temperature photoluminescence from amorphous silicon nanoparticles in SiOx thin films. Journal of Luminescence, 2007, 126, 497-502.	3.1	14
43	Stress and Displacement in Cantilever-Based Transducers for Biosensing Application. , 2006, , .		1
44	Integrated optical proximity microsensor. Journal of Luminescence, 2006, 121, 394-398.	3.1	2
45	Nanocrystalline Layers of CdSe Produced by Means of a Multilayer Approach. , 2004, , 115-125.		0
46	Title is missing!. Journal of Materials Science: Materials in Electronics, 2003, 14, 799-800.	2.2	5
47	Raman scattering and photoluminescence from Si nanoparticles in annealed SiOx thin films. Journal of Applied Physics, 2002, 92, 4678-4683.	2.5	182
48	Composition, structure and annealing-induced phase separation in SiOx films produced by thermal evaporation of SiO in vacuum. Vacuum, 2002, 68, 1-9.	3.5	46
49	MOS Structures Containing Si Nanocrystals for Applications in UV Dosimeters. Key Engineering Materials, 0, 605, 380-383.	0.4	1
50	Silicon Oxide Films Containing Amorphous or Crystalline Silicon Nanodots for Device Applications. , 0, , .		1